



20V N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON) MAX}	Package	I _D T _A = +25°C
	11mΩ @ V _{GS} = 4.5V	U-DFN2020-6 (Type E)	10.5A
20V	13mΩ @ V _{GS} = 2.5V	U-DFN2020-6 (Type E)	9.4A
200	30mΩ @ V _{GS} = 1.8V	U-DFN2020-6 (Type E)	6.5A
	50mΩ @ V _{GS} = 1.5V	U-DFN2020-6 (Type E)	5.5A

Description

This new generation MOSFET has been designed to minimize the onstate resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- General Purpose Interfacing Switch
- Power Management Functions

Features

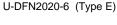
- 0.6mm Profile Ideal for Low Profile Applications
- PCB Footprint of 4mm²
- Low Gate Threshold Voltage
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The DMN2013UFDEQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.

https://www.diodes.com/quality/product-definitions/

Mechanical Data

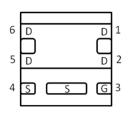
- Case: U-DFN2020-6
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (4)
- Weight: 0.0065 grams (Approximate)



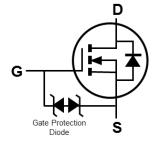




Bottom View



Pin Out



Equivalent Circuit

Ordering Information (Note 4)

Part Number	Compliance	Case	Quantity per Reel
DMN2013UFDEQ-7	Automotive	U-DFN2020-6 (Type E)	3,000
DMN2013UFDEQ-13	Automotive	U-DFN2020-6 (Type E)	10.000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.



Marking Information

Site 1



N6 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: H = 2020) M = Month (ex: 9 = September)

Date Code Key

Year	2020	2021	2022	2023	2024	2025	2026	2027	2028	2029	2030	2031
Code	Н	ı	J	K	L	М	N	0	Р	R	S	Т
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec

Site 2



N6 = Product Type Marking Code YWX = Date Code Marking Y = Year (ex: 0 = 2020) W = Week (ex: a = week 27; z Represents Week 52 and 53) X = Internal Code (ex: U = Monday)

Date Code Key

Year	2020	2021	2022	2023	2024	2025	2026	2027	2028	2029	2030	2031
Code	0	1	2	3	4	5	6	7	8	9	0	1

Week	1-26	27-52	53
Code	A-Z	a-z	Z

Internal Code	Sun	Mon	Tue	Wed	Thu	Fri	Sat
Code	Т	U	V	W	X	Υ	Z



Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage			V _{DSS}	20	V
Gate-Source Voltage			V _{GSS}	±8	V
Continuous Drain Current (Note CV)	Steady State	$T_A = +25$ °C $T_A = +70$ °C	I _D	10.5 8.5	А
Continuous Drain Current (Note 6) V _{GS} = 4.5V	t < 10s	$T_A = +25$ °C $T_A = +70$ °C	I _D	12.5 10.0	А
Continuous Dunis Courset (Note CV)	Steady State	T _A = +25°C T _A = +70°C	I _D	9.4 7.5	А
Continuous Drain Current (Note 6) V _{GS} = 2.5V	t < 10s	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I _D	11.2 8.8	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%	I _{DM}	80	Α		
Maximum Body Diode Continuous Current			Is	2.5	Α

Thermal Characteristics

Characteristic		Symbol	Value	Unit	
Total Power Dissipation (Note 5)	$T_A = +25^{\circ}C$	Pn	0.66	W	
Total Power Dissipation (Note 5)	$T_A = +70^{\circ}C$	PD	0.42	VV	
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	ם	189	°C/W	
Thermal Resistance, Junction to Ambient (Note 3)	t<10s	$R_{ heta JA}$	132	0/ ٧٧	
Total Power Dissipation (Note 6)	$T_A = +25$ °C	Pn	2.03	W	
Total Fower Dissipation (Note o)	$T_A = +70^{\circ}C$	FD	1.31	VV	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	ב	61		
Thermal Resistance, Junction to Ambient (Note 0)	t<10s	$R_{\theta JA}$	43	°C/W	
Thermal Resistance, Junction to Case (Note 6)	$R_{ heta JC}$	9.3			
Operating and Storage Temperature Range		$T_{J_i} T_{STG}$	-55 to +150	°C	

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

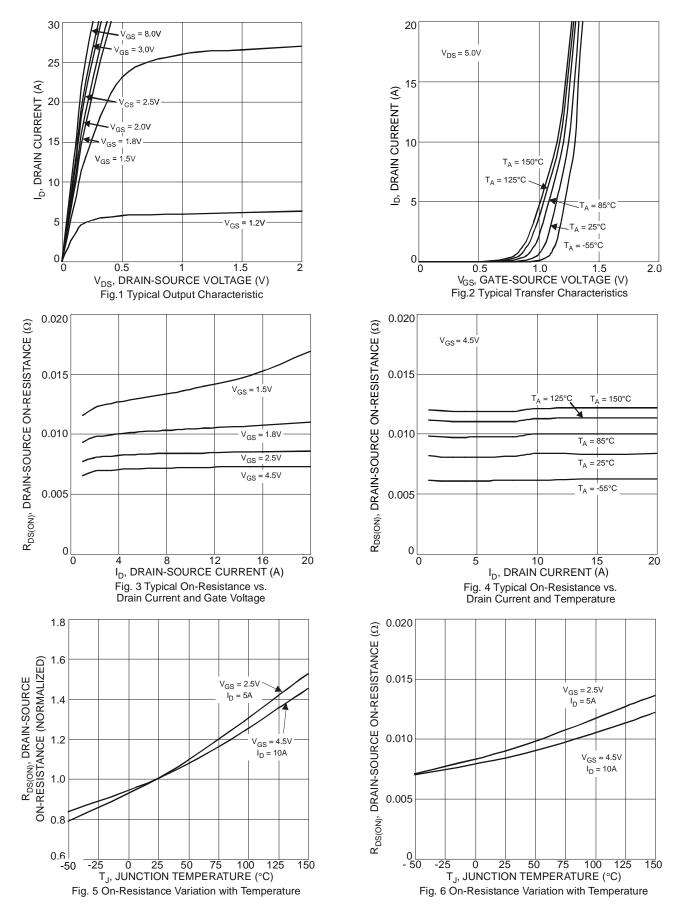
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)					•		
Drain-Source Breakdown Voltage	BV _{DSS}	20	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	_	_	1	μΑ	$V_{DS} = 16V, V_{GS} = 0V$	
Gate-Source Leakage	IGSS	_	_	±2	μΑ	$V_{GS} = \pm 8V$, $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V _{GS(TH)}	0.5	_	1.1	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
			8.4	11		$V_{GS} = 4.5V, I_D = 8.5A$	
Static Drain-Source On-Resistance	_		9.8	13		$V_{GS} = 2.5V, I_D = 8.5A$	
Static Drain-Source On-Resistance	R _{DS(ON)}	_	12	30	mΩ	$V_{GS} = 1.8V, I_D = 1A$	
			15	50		$V_{GS} = 1.5V, I_D = 0.5A$	
Forward Transfer Admittance	Y _{fs}	_	10	_	S	$V_{DS} = 5V, I_{D} = 4A$	
Diode Forward Voltage	V _{SD}	_	-	1.2	V	$V_{GS} = 0V, I_{S} = 8.5A$	
DYNAMIC CHARACTERISTICS (Note 8)					•		
Input Capacitance	C _{iss}	_	2453	_	pF		
Output Capacitance	Coss	_	275	_	pF	$V_{DS} = 10V, V_{GS} = 0V,$ - f = 1.0MHz	
Reverse Transfer Capacitance	Crss	_	257	_	pF	T = T.OIVINZ	
Gate Resistance	Rq	_	1.2	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = 4.5V)	Qg	_	14.3	_	nC		
Total Gate Charge (V _{GS} = 8V)	Qq	_	25.8	_	nC	V 40V L 0.5A	
Gate-Source Charge	Q_{gs}	_	1.8	_	nC	$V_{DS} = 10V, I_{D} = 8.5A$	
Gate-Drain Charge	Q_{gd}	_	2.1	_	nC	1	
Turn-On Delay Time	t _{D(ON)}	_	9.9	_	ns		
Turn-On Rise Time	t _R	_	24.5	_	ns	$V_{DS} = 10V, I_D = 8.5A$	
Turn-Off Delay Time	t _D (OFF)	_	66.4	_	ns	$V_{GS} = 4.5V, R_{G} = 1.8\Omega$	
Turn-Off Fall Time	t _F	_	20.8	_	ns	1	

Notes: 5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.

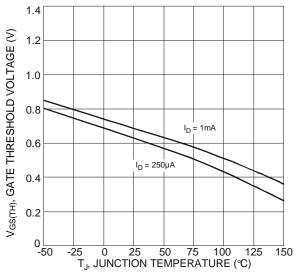
- 6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
- 7. Short duration pulse test used to minimize self-heating effect.
- 8. Guaranteed by design. Not subject to production testing.

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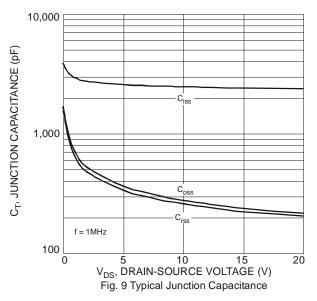


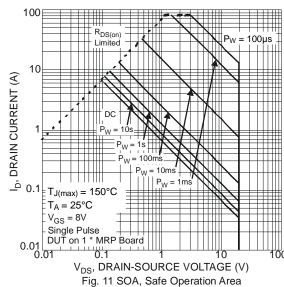


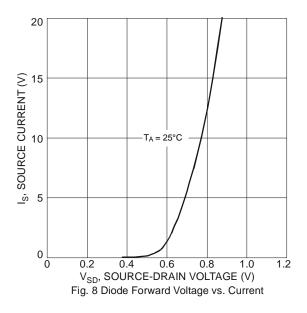


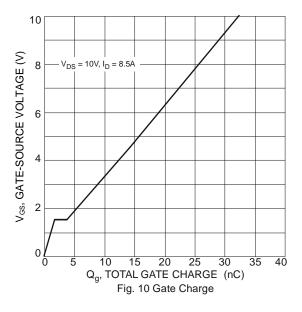




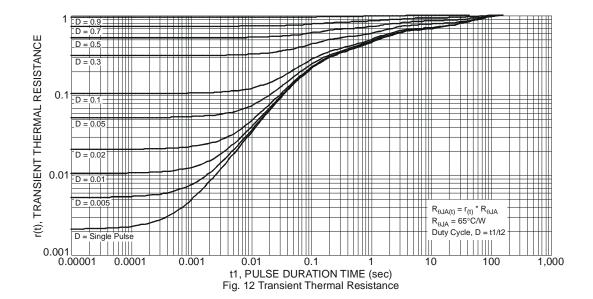










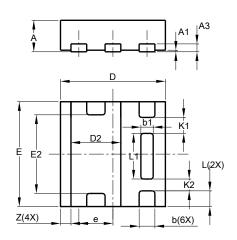




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN2020-6 (Type E)

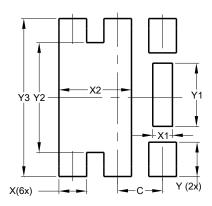


	U-DFN2020-6								
	Type E Dim Min Max Typ								
Dim	Min	Min Max							
Α	0.57	0.63	0.60						
A1	0	0.05	0.03						
A3	_	-	0.15						
b	0.25	0.35	0.30						
b1	0.185	0.285	0.235						
D	1.95	2.05	2.00						
D2	0.85	1.05	0.95						
Е	1.95 2.05		2.00						
E2	1.40	1.60	1.50						
е	_	-	0.65						
L	0.25	0.35	0.30						
L1	0.82	0.92	0.87						
K1	_	_	0.305						
K2	_	_	0.225						
Z	-	_	0.20						
All	Dimen	sions i	in mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN2020-6 (Type E)



Dimensions	Value (in mm)
С	0.650
Х	0.400
X1	0.285
X2	1.050
Y	0.500
Y1	0.920
Y2	1.600
Y3	2.300



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